

MCP2050

LIN Transceiver with Voltage Regulator

Features:

- The MCP2050 is compliant with:
- LIN Bus Specifications Version 1.3, 2.1 and with SAE J2602-2
- · Support Baud Rates Up to 20 kBaud
- · 43V Load Dump Protected
- Maximum Continuous Input Voltage of 30V
- Wide LIN Compliant Supply Voltage, 6.0-18.0V
- Extended Temperature Range: -40 to +125°C
- Interface to PIC[®] EUSART and Standard USARTs
- Wake-Up on LIN Bus Activity or Local Wake Input
- · LIN Bus Pin
 - Internal pull-up termination resistor and diode for slave node
 - Protected against VBAT shorts
 - Protected against loss of ground
- High current drive
- TXD and LIN Bus Dominant Time-Out Function
- Two Low-Power Modes
 - Transmitter Off mode: 90 µA (typical)
 - Power Down mode: 4.5 µA (typical)
- Output Indicating Internal Reset State (POR or Sleep Wake)
- MCP2050 On-Chip Voltage Regulator
 - Output voltage of 5.0V or 3.3V with 70 mA capability and tolerances of ±3% over operating temperature range
 - Internal short-circuit current limit
 - Only external filter and load capacitors needed
- Programmable Windowed Watchdog Timer (WWDT)
 - External resistor programmable from 7 ms to 140 ms
 - Disabled by connecting the WWDTSELECT pin to VREG or let the pin float
- Ratiometric Output of VBAT Voltage Scaled to VREG
- Automatic Thermal Shutdown
- High Electromagnetic Immunity (EMI), Low Electromagnetic Emission (EME)
- Robust ESD Performance: ±15 kV for LBUS and VBB pin (IEC61000-4-2)
- Transient Protection for LBUS and VBB Pins in Automotive Environment (ISO7637)

- Meets Stringent Automotive Design Requirements Including "OEM Hardware Requirements for LIN, CAN and FlexRay Interfaces in Automotive Applications", Version 1.3, May 2012
- Multiple Package Options Including Small 5x5 QFN

Description:

The MCP2050 provides a bidirectional, half-duplex communication physical interface to meet the LIN bus specification Revision 2.1 and SAE J2602. The device incorporates a voltage regulator with 5V or 3.3V 70 mA regulated power supply output. The on-chip WWDT allows users to adjust the size of the reset window by using an external resistor. The ratiometric VBAT pin scales down VBAT to the range of VREG so it can be monitored by an A/D converter.

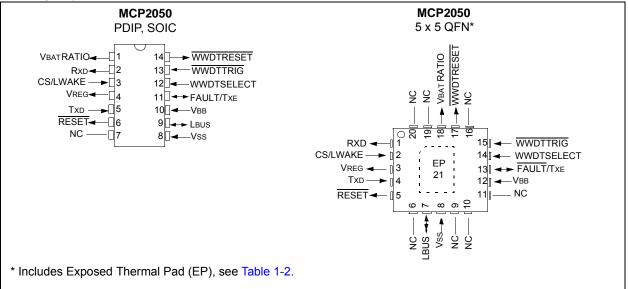
The device has been designed to meet the stringent quiescent current requirements of the automotive industry and will survive +43V load dump transients, and double battery jumps.

MCP2050 family members:

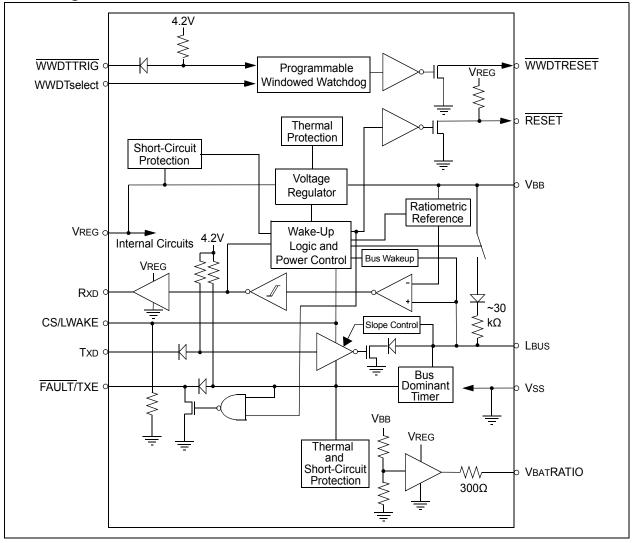
- MCP2050-500, 14-pin, LIN driver with 5.0V regulator
- MCP2050-330, 14-pin, LIN driver with 3.3V regulator
- MCP2050-500, 20-pin QFN, LIN driver with 5.0V regulator
- MCP2050-330, 20-pin QFN, LIN driver with 3.3V regulator



Package Types



Block Diagram



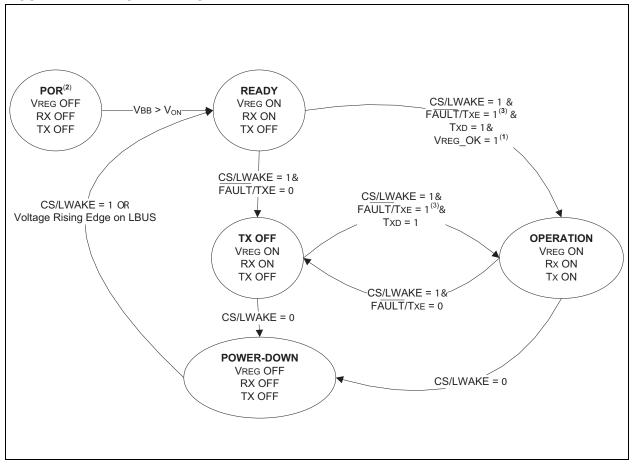
1.0 FUNCTION DESCRIPTION

The MCP2050 provides a physical interface between a microcontroller and a LIN half-duplex bus. It is intended for automotive and industrial applications with serial bus baud rates up to 20 kbaud. This device will translate the CMOS/TTL logic levels to LIN logic levels, and vice versa. The device offers optimum EMI and ESD performance; it can withstand high voltage on the LIN bus. The device supports two low-power modes to meet automotive industry power consumption requirements. The MCP2050 also provides a +5V or 3.3V 70 mA regulated power output.

FIGURE 1-1: STATE DIAGRAM

1.1 Modes of Operation

The MCP2050 works in five modes: Power-On Reset mode, Power-Down mode, Ready mode, Operation mode, and Transmitter Off mode. For an overview of all operational modes, please refer to Table 1-1. For the operational mode transition, please refer to Figure 1-1.



Note 1: VREG_OK: Regulator Output Voltage > 0.8VREG_NOM.

- 2: If the voltage on pin VBB falls below VOFF, the device will enter Power-On Reset mode from all other modes, which is not shown in the figure.
- **3:** FAULT/TXE = 1 represents input and no fault conditions. FAULT/TXE = 0 represents input low or a fault condition. Refer to Table 1-3.

1.1.1 POWER-ON-RESET MODE

Upon application of VBB, or whenever the voltage on VBB is below the threshold of regulator turn-off voltage VOFF (typically. 4.50V), the device enters Power-On Reset mode (POR). During this mode, the device maintains the digital section in a reset mode and waits until the voltage on pin VBB rises above the threshold of regulator turn-on voltage VON (typically 5.75V) to enter into Ready mode. In Power-On-Reset mode, the LIN physical layer and voltage regulator are disabled, and RESET output is forced to low.

1.1.2 READY MODE

The device enters Ready mode from POR mode after the voltage on VBB rises above the threshold of regulator turn-on voltage VON or from Power-Down mode when a remote or local wake-up event happens.

Upon entering Ready mode, the voltage regulator and receiver section of the transceiver are powered up. The transmitter remains in off state. The device is ready to receive data but not to transmit. In order to minimize the power consumption, the regulator operates in a reduced-power mode. It has a lower GBW product and thus is slower. However, the 70 mA drive capability is unchanged.

The device stays in Ready mode until the output of the voltage regulator has stabilized and the CS/LWAKE pin is high ('1').

1.1.3 OPERATION MODE

If VREG is OK (VREG > 0.8 VREG_NOM), CS/LWAKE pin, FAULT/TXE pin and TXD pin are high, the part enters the Operation mode from either Ready or Transmitter Off mode.

In this mode, all internal modules are operational. The internal pull-up resistor between LBUS and VBB is connected only in this mode.

The device goes into the Power-Down mode at the falling edge on CS/LWAKE; or to the Transmitter Off mode at the falling on FAULT/TXE while CS/LWAKE stays high.

1.1.4 TRANSMITTER OFF MODE

In Transmitter Off mode, the receiver is enabled but the LBUS transmitter is off. It is a lower-power mode.

In order to minimize the power consumption, the window watchdog timer is disabled and the regulator operates in a reduced-power mode. It has a lower GBW product and thus is slower. However, the 70 mA drive capability is unchanged.

The transmitter may be re-enabled whenever the FAULT/TxE signal returns high, by removing the internal fault condition and the CPU returning the FAULT/TxE high. The transmitter will not be enabled even if the FAULT/TxE pin is brought high externally, when the internal fault is still present. However, externally forcing the FAULT/TxE high, while the internal fault is still present, should be avoided since this will induce high current and power dissipation in the FAULT/TxE pin.

The transmitter is also turned off whenever the voltage regulator is unstable or recovering from a fault. This prevents unwanted disruption of the bus during times of uncertain operation.

1.1.5 POWER-DOWN MODE

In Power-Down mode, the transceiver and the voltage regulator are both off. Only the Bus Wake-up section and the CS/LWAKE pin wake-up circuits are in operation. This is the lowest-power mode.

If any bus activity (e.g. a BREAK character) occurs during Power-Down mode, the device will immediately enter Ready mode and enable the voltage regulator. Then, once the regulator output has stabilized (approximately 0.3 ms to 1.2 ms) it goes to Operation mode. Refer to **Section 1.1.6 "Remote Wake-up"** for more details.

The part will also enter Ready mode from Power-Down mode, followed by Operation mode, if the CS/LWAKE pin becomes active high ('1').

1.1.6 REMOTE WAKE-UP

The remote wake-up sub module observes the LBUS in order to detect bus activity. In Power-Down mode, normal LIN recessive/dominant threshold is disabled, and the LIN bus Wake-Up Voltage Threshold VWK(LBUS) is used to detect bus activities. Bus activity is detected when the voltage on the LBUS falls below the LIN bus Wake-Up Voltage Threshold VWK(LBUS) (approximately 3.4V) for at least tBDB (a typical duration of 80 μ s) followed by a rising edge. Such a condition causes the device to leave Power-Down mode

State	Transmitter	Receiver	Internal Wake Module	Voltage Regulator	Watch Dog Timer	Operation	Comments
PoR	Off	Off	Off	Off	Off	Proceed to Ready mode after V _{BB} >V _{ON} .	—
Ready	Off	On	Off	On	On	If CS/LWAKE high, then proceed to Operation or Transmitter Off mode.	Bus Off state
Operation	On	On	Off	On	On	If CS/LWAKE low level, then proceed to Power-Down. If FAULT/TXE low level, then Transmitter-Off mode.	Normal Operation mode
Power-Down	Off	Off	On Activity Detect	Off	Off	On LIN bus rising edge or CS/LWAKE high level, proceed to READY mode.	Lowest- Power mode
Transmitter Off	Off	On	Off	On	Off	If CS/LWAKE low level, then proceed to P <u>ower d</u> own. If FAULT/TXE high, then Operation mode.	Bus Off state, Lower-Power mode

 TABLE 1-1:
 OVERVIEW OF OPERATIONAL MODES

1.2 Windowed Watchdog Reset

The Watchdog Timer monitors for activity on the Windowed Watchdog Timer Trigger input pin WWDTTRIG. The WWDTTRIG pin is expected to be strobed within a given time frame. When this time frame has expired without an edge transition on the WWDTTRIG pin, the WWDTRESET pin is driven active (low) to reset the system. This feature is enabled by connecting a resistor between the WWDTSELECT pin and Vss. Monitoring is then done by requiring the host processor to force a falling edge transition on the WWDTTRIG pin within a predetermined time frame (Twp).

The start time of the trigger window is fixed at 50% of the total watchdog period, after the last trigger. The length of the window is determined by the value of the resistor on pin WWDTSELECT. The Watchdog Timer is disabled if WWDTSELECT is floating.

1.2.1 WWDT DURING INITIAL POWER-UP

The WWDTRESET is driven high after a power-on reset. The Watchdog Timer begins counting at this point, awaiting an edge on WWDTTRIG pin. Note that there is no window enabled, yet. If no falling edge is detected on the WWDTTRIG pin before the timer expires, the WWDTRESET is pulse low and the timer is restarted. When a trigger edge on the WWDTTRIG pin is seen, the window is enabled and the timer is reset.

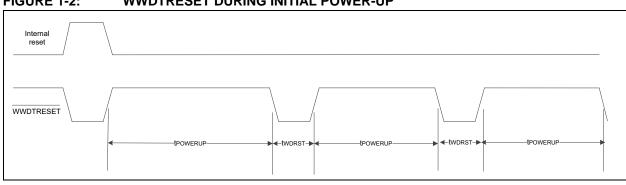


FIGURE 1-2: WWDTRESET DURING INITIAL POWER-UP

Figure 1-2 shows the behavior of the WWDTRESET pin after a system reset with no trig at all. If no trig is given during the power-up window, WWDTRESET is reset low for the time tWDRST.

The power-up window length tPOWERUP duration is determined by the value of the resistor connected between pin WWDTSELECT and pin Vss, while the reset pulse duration is about 150 µs.

Duration for tPOWERUP and tWDRST are:

- tPOWERUP = 0.8 ms x (RwwDTSELECT+1) typical
- tworst = 150 µs typical
- RWWDTSELECT is in kΩ.

Once a trig is asserted, the power-up sequence "stops" and the normal behavior begins.

1.2.2 WINDOWED WATCHDOG BEHAVIOR

After windowed watchdog begins its normal behavior, three different cases can appear.

- A pulse (falling edge) on the WWDTTRIG pin is detected within the trigger window; the watchdog timer will be reset, and a new watchdog period will begin; WWDTRESET pin remains high (Figure 1-3.)
- A pulse (falling edge) on the WWDTTRIG pin is detected before the trigger window (too early trigger); WWDTRESET is asserted (low) immediately after the falling edge is detected for approximately t_{WDRST}; the counter is reset and the next watchdog period begins at the rising edge of the voltage on WWDTRESET pin (Figure 1-12).
- No pulse on the WWDTTRIG pin is detected during the whole watchdog window (no trigger); WWDTRESET is asserted (low) for approximately twDRST when the timer has expired; the counter is reset and the next watchdog period begins at the rising edge of the voltage on WWDTRESET pin (Figure 1-5).

The trigger window is between 50% to 100% of the watchdog window length, twLENGTH. The window length is determined by the external resistor between WWDTSELECT pin and Vss.

FIGURE 1-3: CORRECT TRIGGER

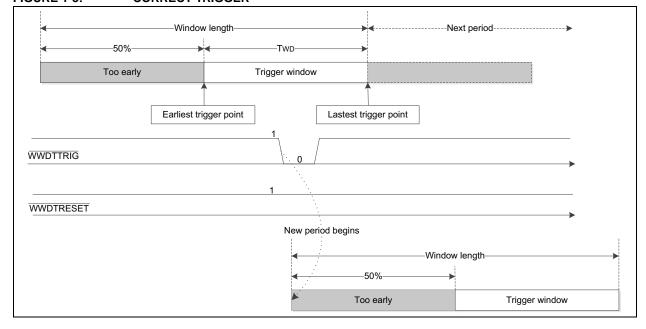
EQUATION 1-1:

tWLENGTH = (0.175 ms × RWWDTSELECT) + 1.2 typical

tworst = 150 µs typical

RWWDTSELECT is in k Ω ; its value ranges from 33 k Ω to 680 k Ω and window length ranges from 7 ms to 120 ms typical.

If the WWDTSELECT pin is floating, the watchdog is disabled and the WWDTRESET remains high.





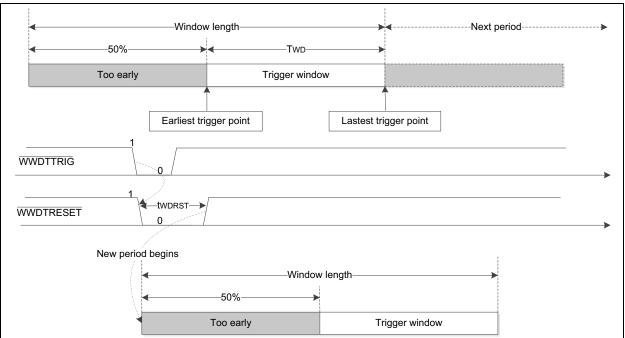
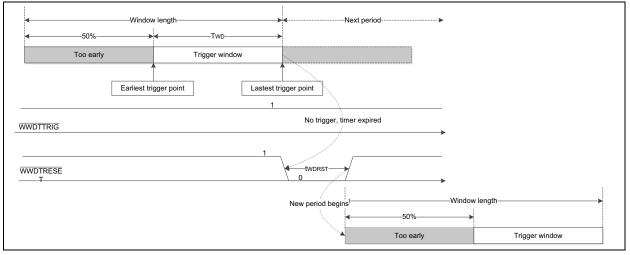


FIGURE 1-5: NO TRIGGER



1.3 Pin Descriptions

Please refer to Table 1-2 for the pinout overview.

TABLE 1-2:	PINOUT DESCRIPTIONS
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	Devi	ces		Function		
PIN Name	14-Pin PDIP, SOIC	5 x 5 QFN	РІ Туре	Normal Operation		
VBATRATIO	1	18	Analog Output	VBATRATIO = VBAT/24 × VREG		
Rxd	2	1	Output	Receive Data Output		
CS/LWAKE	3	2	TTL Input, HV-tolerant	Chip Select and Local Wake-up Input		
VREG	4	3	Output	Voltage Regulator Output		
Txd	5	4	Input, HV-tolerant	Transmit Data Input		
RESET	6	5	Output	Reset Output		
NC	7	6,9,10,11, 16,19,20	Not Connected	—		
Vss	8	8	Power	Ground		
LBUS	9	7	I/O, HV	LIN Bus		
VBB	10	12	Power	Battery		
FAULT/TXE	11	13	I/O, HV-tolerant	Fault Detect Output/Transmitter Enable Input		
WWDTSELECT	12	14	Input	A Resistor between this pin and Ground determines the Watchdog Window length		
WWDTTRIG	13	15	Input	Windowed Watchdog Trigger Input		
WWDTRESET	14	17	Output, HV-tolerant	Windowed Watchdog Reset Output		
EP	—	21	Exposed Thermal Pad (EP)	Exposed Thermal Pad can be left unconnected, or connected to the ground.		

1.3.1 VBATRATIO

This is an analog output pin that reflects the voltage at the VBAT pin. It is scaled by VREG such that:

VBATRATIO = VBAT/24 × VREG

0 <= VBATRATIO <= VREG

The resistive divider and the output driver are switched off during Power-Down mode in order to reduce power consumption.

1.3.2 RxD

Receive Data Output pin. The RxD pin is a standard CMOS output pin and it follows the state of the LBUS pin.

1.3.3 CS/LWAKE

Chip Select and Local Wake-Up Input pin (TTL level, high voltage tolerant). This pin controls the device state transition. Refer to Figure 1-1.

If CS/LWAKE = 1, the device can work in Operation mode (FAULT/TxE = 1) or Transmitter Off mode (FAULT/TxE = 0).

If CS/LWAKE = 0, the device can work in Power-Down mode or Ready mode.

An internal pull-down resistor will keep the CS/LWAKE pin low to ensure that no disruptive data will be present on the bus while the microcontroller is executing a Power-on Reset and I/O initialization sequence. When CS/LWAKE is '1', a weak pull-down (~600 kΩ) is used to reduce current. When CS/LWAKE is '0' a stronger pull-down (~300 kΩ) is used to maintain the logic level.

This pin may also be used as a local wake-up input (see Figure 1-12). The microcontroller will set the I/O pin to control the CS/LWAKE. An external switch, or other source, can then wake-up both the transceiver and the microcontroller.

Note: CS/LWAKE should NOT be tied directly to pin VREG as this could force the MCP2050 into Operation Mode before the microcontroller is initialized.

1.3.4 VREG

Positive Supply Voltage Regulator Output pin. An onchip LDO gives +5.0 or +3.3V 70 mA regulated voltage on this pin.

1.3.5 Txd

Transmit Data Input pin (TTL level, HV compliant, adaptive pull-up). The transmitter reads the data stream on TxD pin and sends it to LIN bus. The LBUS pin is low (dominant) when TxD is low, and high (recessive) when TxD is high.

The Transmit Data Input pin has an internal adaptive pull-up to an internally-generated 4.2V (approximate). When TxD is '0', a weak pull-up (~900 k Ω) is used to reduce current. When TxD is '1' a stronger pull-up (~300 k Ω) is used to maintain the logic level. A series reverse-blocking diode allows applying TxD input voltages greater than the internally generated 4.2V and renders TxD pin HV compliant up to 30V (see the Block Diagram on page 2).

1.3.6 RESET

Reset Output pin. This pin is open drain with ~90 k Ω pull-up to VREG. It indicates the internal voltage has reached a valid, stable level. As long as the internal voltage is valid (above 0.8VREG), this pin will remain high ('1'); otherwise the RESET pin switches to low ('0').

1.3.7 Vss

Ground pin.

1.3.8 LBUS

LBUS is a bidirectional LIN bus Interface pin and is controlled by the signal TxD. It has an open collector output with a current limitation. To reduce electromagnetic emission, the slopes during signal changes are controlled, and the LBUS pin has corner-rounding control for both falling and rising edges.

The internal LIN receiver observes the activities on LIN bus, and generates the output signal RxD that follows the state of the LBUS. A first degree 160 kHz, low-pass input filter optimizes electromagnetic immunity.

1.3.9 Vbb

Battery Positive Supply Voltage pin. An external diode is connected in series to prevent the device from being reversely powered (refer Figure 1-12).

1.3.10 FAULT/TXE

Fault Detect Output/Transmitter Enable Input pin. The output section is HV tolerant open drain (up to 30V). The input section is identical with TxD section (TTL level, HV compliant, adaptive pull-up). The internal pull-up resistor may be too weak for some applications. An external 10k Ω pull-up resistor is recommended to ensure a logic high level. Its state is defined as shown in Table 1-3. The device is placed in Transmitter Off mode whenever this pin is low ('0'), either from an internal fault condition or by external drive.

If CS/LWAKE is high ('1'), the FAULT/TxE signals a mismatch between the TxD input and the LBUS level. This can be used to detect a bus contention. Since the bus exhibits a propagation delay, the sampling of the internal compare is debounced to eliminate false faults.

After the device wakes up, the \overline{FAULT}/TxE indicates what wakes the device if CS/LWAKE remains low ('0') (refer to Table 1-3).

The FAULT/TxE pin sampled at a rate faster than every 10 $\mu s.$

1.3.11 WWDTSELECT

This is an analog input pin that sets the open window time to accept a trigger reset. A resistor between this pin and Vss sets this time. The equation to determine the value of the resistor can be found in Section 1.2.2 "Windowed Watchdog Behavior".

1.3.12 WWDTTRIG

This is an input pin to reset the Windowed Watchdog Timer. A high-to-low transition during the open window time will reset the timer and prevent the WWDT from timing out. The pin has an internal adaptive pull-up to an internally-generated 4.2V (approximate.).

When $\overline{WWDTTRIG}$ is '0', a weak pull-up (~800 k Ω) is connected to reduce current.

When $\overline{WWDTTRIG}$ is '1', the pull-up is stronger to maintain the logic level.

1.3.13 WWDTRESET

WWDTRESET is an open-drain output pin. This pin is asserted low when the internal Windowed Watchdog Timer has expired or an attempt was made to clear the timer before the window has opened.

1.3.14 EP

It is recommended to connect this pad to Vss to enhance electromagnetic immunity and thermal resistance.

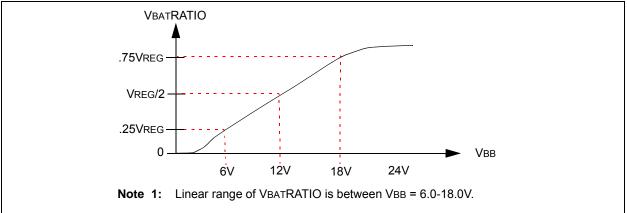
Тхр	RxD	LIN BUS	Thermal	FAULT/Txe				
In	Out	I/O	Override	External Input	Driven Output	Definition		
				CS	= 1			
L	Н	VBB	OFF	Н	L	FAULT , TXD driven low, LBUS shorted to VBB (Note 1), or LBUS/TXD permanent dominant detected, and transmit time-out shutdown.		
Н	Н	VBB	OFF	Н	Н	ОК		
L	L	GND	OFF	Н	Н	ОК		
Н	L	GND	OFF	Н	Н	OK, data is being received from LBUS		
х	х	VBB	ON	Н	L	FAULT, transceiver in thermal shutdown		
х	x	VBB	Х	L	х	NO FAULT , the CPU is commanding the transceiver to turn off the transmitter driver		
	CS = 0 after a wake-up							
Х	х	х	х	х	L	Wake-up from LIN bus activity		
х	х	х	х	х	Н	Wake-up from POR		

TABLE 1-3: FAULT/TXE TRUTH TABLE

Legend: x = don't care

Note 1: The FAULT/TXE is valid after approximately 25 µs after TXD falling edge. This is to eliminate false fault reporting during bus propagation delays.

FIGURE 1-6: VBATRATIO OUTPUT RANGE



1.4 Fail-Safe Features

1.4.1 GENERAL FAIL-SAFE FEATURES

- An internal pull-down resistor on the CS/LWAKE pin disables the transmitter if the pin is floating.
- An internal pull-up resistor on the TxD pin places TxD in high, thus the LBUS is recessive if the TxD pin is floating.
- High-Impedance and low leakage current on LBUS during loss of power or ground.
- The current limit on LBUS protects the transceiver from being damaged if the pin is shorted to VBB.

1.4.2 THERMAL PROTECTION

The thermal protection circuit monitors the die temperature and is able to shut down the LIN transmitter and voltage regulator.

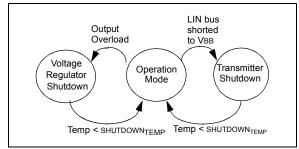
There are three causes for a thermal overload. A thermal shut down can be triggered by any one, or a combination of, the following thermal overload conditions.

- · Voltage regulator overload
- · LIN bus output overload
- Increase in die temperature due to increase in environment temperature

The recovery time from the thermal shutdown is equal to adequate cooling time.

Driving the TxD and checking the RxD pin makes it possible to determine whether there is a bus contention (TxD = high, RxD = low) or a thermal overload condition (TxD = low, RxD = high).

FIGURE 1-7: THERMAL SHUTDOWN STATE DIAGRAMS



1.4.3 Txd/LBUS TIME-OUT TIMER

LIN bus can be driven to a dominant level either from TxD pin or externally. An internal timer deactivates the LBUS transmitter if a dominant status (low) on LIN bus lasts longer than Bus Dominant Time-Out Time tTO(LIN) (approximately 20 ms); at the same time, RXD output is put in recessive (high), FAULT/TXE is also driven to low and the internal LIN pull-up resistor is disconnected. The timer is reset on any recessive LBUS status or POR mode. The recessive status on LBUS can be caused either by the bus being externally pulled up or by TXD pin being returned high.

1.5 Internal Voltage Regulator

The MCP2050 has a positive regulator capable of supplying +5.0V or +3.3V at up to 70 mA of load current with tolerances of $\pm 3\%$ over the entire operating temperature range of -40°C to +125°C. The regulator uses an LDO design, is short-circuit-protected and will turn the regulator output off if its output falls below the Shutdown Voltage Threshold VSD.

With a load current of 70 mA, the minimum input-tooutput voltage differential required for the output to remain in regulation is typically +0.5V (+1V maximum over the full operating temperature range). Quiescent current is less than 100 μ A with a full 70 mA load current when the input-to-output voltage differential is greater than +3.00V.

Regarding the correlation between VBB, VREG and IDD, refer to Figure 1-9 and Figure 1-10. When the input voltage (VBB) drops below the differential needed to provide stable regulation, the voltage regulator output VREG will track the input down to approximately VOFF. The regulator will turn off the output at this point. This will allow PIC[®] microcontrollers, with internal POR circuits, to generate a clean arming of the Power-on Reset trip point. The MCP2050 will then monitor VBB and turn on the regulator when VBB is above the threshold of regulator turn-on voltage VON.

Under specific ambient temperature and battery voltage range, the voltage regulator can output as high as 150 mA current.

For current load capability of the voltage regulator, refer to Figure 1-9 and Figure 1-10.

In Power-Down mode, the VBB monitor is turned off.

Note: The regulator overload current limit is approximately 250 mA. The regulator output voltage VREG is monitored. If output voltage VREG is lower than VSD, the voltage regulator will turn off. After a recovery time of about 3 ms, the VREG will be checked again. If there is no short circuit, (VREG > VSD) then the voltage regulator remains on.

The regulator requires an external output bypass capacitor for stability. See Figure 2-1 for correct capacity and ESR for stable operation.

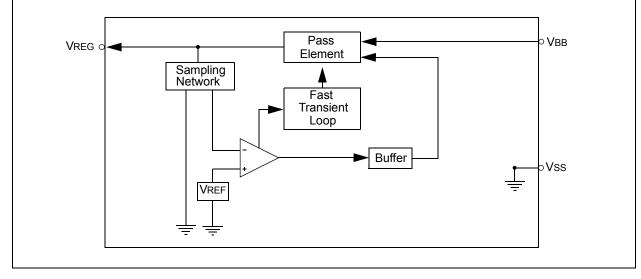
Note:	A ceramic capacitor of at least 10 µF, or a
	tantalum capacitor of at least 2.2 µF is
	recommended for stability.

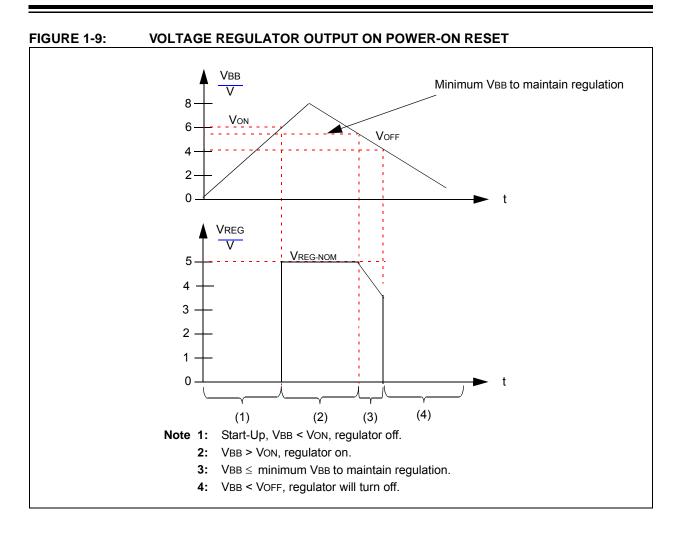
Warning: In worst-case scenarios, the ceramic capacitor may derate by 50%, based on tolerance, voltage and temperature. Therefore, in order to ensure stability, ceramic capacitors smaller than 10 μF may require a small series resistance to meet the ESR requirements, as shown in Table 1-4.

TABLE 1-4: RECOMMENDED SERIES RESISTANCE FOR CERAMIC CAPACITORS

Resistance	Capacitor
1Ω	1 µF
0.47Ω	2.2 µF
0.22Ω	4.7 µF
0.1Ω	6.8 µF

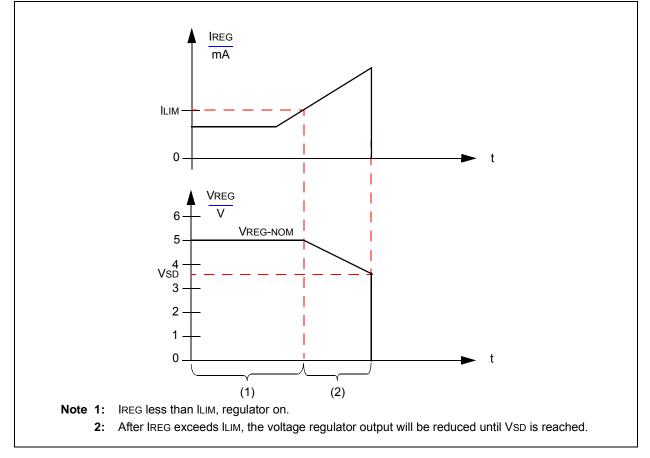
FIGURE 1-8: VOLTAGE REGULATOR BLOCK DIAGRAM





MCP2050

FIGURE 1-10: VOLTAGE REGULATOR OUTPUT ON OVER CURRENT SITUATION



1.6 Optional External Protection

1.6.1 REVERSE BATTERY PROTECTION

An external reverse-battery-blocking diode should be used to provide polarity protection (see Figure 1-12).

1.6.2 TRANSIENT VOLTAGE PROTECTION (LOAD DUMP)

An external 43V transient suppressor (TVS) diode, between VBB and ground, with a transient protection resistor (RTP) in series with the battery supply and the VBB pin protects the device from power transients and ESD events greater than 43V (see Figure 1-12). The maximum value for the RTP protection resistor depends on two parameters: the minimum voltage the part will start at, and the impacts of this RTP resistor on the VBB value, thus on the Bus recessive level and slopes.

This leads to a set of three equations to fulfill.

Equation 1-2 provides a max RTP value according to the minimum battery voltage the user wants the part to start at.

Equation 1-3 provides a max RTP value according to the maximum error on the recessive level thus VBB since the part uses VBB as the reference value for the recessive level.

Equation 1-4 provides a max RTP value according to the maximum relative variation the user can accept on the slope when IREG varies.

Since both Equation 1-2 and Equation 1-3 must be fulfilled, the maximum allowed value for RTP is thus the smaller of the two values found when solving Equation 1-2 and Equation 1-3.

Usually Equation 1-2 gives the higher constraint (smaller value) for RTP as shown in the following example where VBATmin is 8V.

However, the user needs to check that the value found with Equation 1-2 also fulfills Equation 1-3 and Equation 1-4.

While this protection is optional, it should be considered as good engineering practice.

EQUATION 1-2:

$$R_{TP} \le \frac{V_{BATmin} - 5.5V}{250mA}$$

 $5.5V = V_{OFF} + 1.0V$

250 mA is the peak current at power-on when VBB = 5.5V

Assume VBATMIN = 8V. Equation 1-2 shows 10Ω .

EQUATION 1-3:

$$R_{TP} \le \frac{\Delta V_{RECESSIVE}}{I_{REGMAX}}$$

Where:

 $\Delta VRECESSIVE = Maximum variation tolerated on the recessive level$

Assume ΔV RECCESSIVE = 1V and IREGMAX = 50 mA Equation 1-3 shows 20 Ω .

EQUATION 1-4:

$$R_{TP} \leq \frac{\Delta Slope \times (V_{BATMIN} - 1V)}{I_{REGMAX}}$$

Where:
$$\Delta Slope = Maximum variation tolerated on the slope levelIREGMAX = Maximum current the current will provide to the loadVBATMIN > VOFF + 1.0V$$

Assume Δ Slope = 15%, VBATMIN = 8V and IREGMAX = 50 mA. Equation 1-3 shows 20 Ω .

1.6.3 CBAT CAPACITOR

Selecting CBAT = $10 \times CREG$ is recommended. However, this leads to a high-value capacitor. Lower values for CBAT capacitor can be used with respect to some rules. In any case, the voltage at the VBB pin should remain above VOFF when the device is turned on.

The current peak at start-up (due to the fast charge of the CREG and CBAT capacitors) may induce a significant drop on the VBB pin. This drop is proportional to the impedance of the VBAT connection (see Figure 1-12).

The VBAT connection is mainly inductive and resistive. Therefore, it can be modeled as a resistor (RTOT) in series with an inductor (L). RTOT and L can be measured.

The following formula gives an indication of the minimum value of CBAT using RTOT and L:

EQUATION 1-5:

$$\frac{C_{BAT}}{C_{REG}} = \sqrt{\frac{100L^2 + R_{TOT}^2}{1 + L^2 + \frac{R_{TOT}^2}{100}}}$$

Where:

L = Inductor (measured in mH)

RTOT = RLINE + RTP (measured in Ω)

Equation 1-5 allows lower CBAT/CREG values than the 10x ratio we recommend.

Assume that we have a good quality VBAT connection with RTOT = 0.1Ω and L = 0.1 mH.

Solving the equation gives CBAT/CREG = 1.

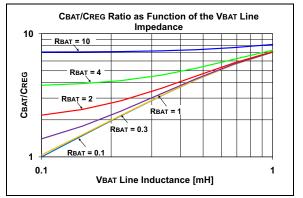
If we increase RTOT up to 1Ω , the result becomes CBAT/CREG = 1.4. However, if the connection is highly resistive or highly inductive (poor connection), the CBAT/CREG ratio greatly increases.

TABLE 1-5:	CBAT/CREG RATIO BY VBAT
	CONNECTION TYPE

Connection Type	Rтот	L	CBAT/CREG Ratio
Good	0.1Ω	0.1 mH	1
Typical	1Ω	0.1 mH	1.4
Highly inductive	0.1Ω	1 mH	7
Highly resistive	10Ω	0.1 mH	7

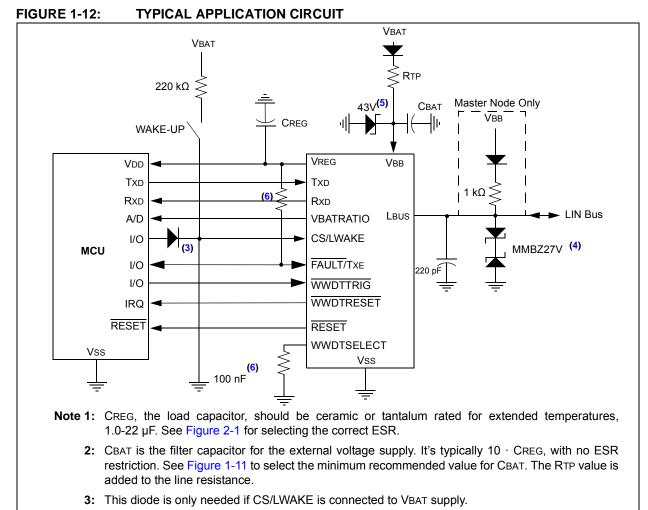
Figure 1-11 shows the minimum recommended CBAT/CREG ratio as a function of the impedance of the VBAT connection.

FIGURE 1-11: MINIMUM RECOMMENDED CBAT/CREG RATIO



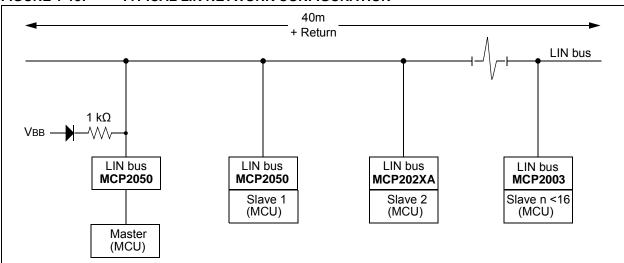
MCP2050

1.7 Typical Applications



- **4:** ESD protection diode.
- 5: This component is for additional load dump protection.
- 6: An external 10 kΩ resistor is recommended for some applications.

FIGURE 1-13: TYPICAL LIN NETWORK CONFIGURATION



1.8 ICSP™ Considerations

The following should be considered when the MCP2050 is connected to pins supporting in-circuit programming:

- Power used for programming the microcontroller can be supplied from the programmer, or from the MCP2050.
- The voltage on the VREG pin should not exceed the maximum value of VREG as shown in Section 2.3, DC Specifications.

2.0 ELECTRICAL CHARACTERISTICS

2.1 Absolute Maximum Ratings†

VIN DC Voltage on RxD, and RESET	0.3V to VREG + 0.3
VIN DC Voltage on TxD, CS/LWAKE, FAULT/TxE	0.3 to + 40V
VBB Battery Voltage, continuous, non-operating (Note 1)	0.3 to + 40V
VBB Battery Voltage, non-operating (LIN bus recessive, no regulator load, t < 60s) (Note 2)	0.3 to + 43V
VBB Battery Voltage, transient ISO 7637 Test 1	
VBB Battery Voltage, transient ISO 7637 Test 2a	+75V
VBB Battery Voltage, transient ISO 7637 Test 3a	150V
VBB Battery Voltage, transient ISO 7637 Test 3b	+100V
VLBUS Bus Voltage, continuous	18 to + 30V
VLBUS Bus Voltage, transient (Note 3)	27 to + 43V
ILBUS Bus Short-Circuit Current Limit	200 mA
ESD protection on LIN, VBB (IEC 61000-4-2) (Note 4)	±15 KV
ESD protection on LIN, VBB (Human Body Model) (Note 5)	±8 KV
ESD protection on all other pins (Human Body Model) (Note 5)	±4 KV
ESD protection on all pins (Charge Device Model) (Note 6)	±1500V
ESD protection on all pins (Machine Model) (Note 7)	±200V
Maximum Junction Temperature	150°C
Storage Temperature	65 to + 150°C

† NOTICE: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

- **Note 1:** LIN 2.x compliant specification.
 - 2: SAE J2602-2 compliant specification.
 - **3:** ISO 7637/1 load dump compliant (t < 500 ms).
 - 4: According to IEC 61000-4-2, 330 ohm, 150 pF and Tranceiver EMC Test Specifications [2] to [4]
 - 5: According to AEC-Q100-002/JESD22-A114
 - 6: According to AEC-Q100-011B
 - 7: According to AEC-Q100-003/JESD22-A115

2.2 Nomenclature used in this document

Some terms and names used in this data sheet deviate from those referred to in the LIN specifications. Equivalent values are shown below.

LIN 2.1 Name	Term used in the following tables	Definition		
VBAT	not used	ECU operating voltage		
VSUP	Vвв	Supply voltage at device pin		
VBUS_LIM	Isc	Current Limit of Driver		
VBUSREC	VIH(LBUS)	Recessive state		
VBUSDOM	VIL(LBUS)	Dominant state		

2.3 DC Specifications

DC Specifications	Electrical Characteristics: Unless otherwise indicated, all limits are specified for: VBB = 6.0V to 18.0V, TA = -40°C to +125°C CREG = 10 µF							
Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions		
Power								
VBB Quiescent Operating Current	IBBQ		—	200	μA	IOUT = 0 mA, LBUS recessive VREG = 5.0V		
		_	-	200	μA	lout = 0 mA, LBUS recessive VREG = 3.3V		
VBB Quiescent Operating Current with Watchdog Enabled	IBBQWDT	_	-	250	μA	lout = 0 mA, LBUS recessive VREG = 5.0V		
				250		lout = 0 mA, LBUS recessive VREG = 3.3V		
VBB READY Current	IBBRD	_	-	100	μA	lout = 0 mA, LBUS recessive VREG = 5.0V		
		_	-	100	μA	IOUT = 0 mA, LBUS recessive VREG = 3.3V		
VBB Ready Current WWDT Enabled	IBBRDWDT	_	—	150	μA	With voltage regulator on, transmitter off, receiver on, FAULT/TxE = VIL, CS = VIH,VREG = 5.0V		
				150		With voltage regulator on, transmitter off, receiver on, FAULT/TxE = VIL, CS = VIH,VREG = 3.3V		
VBB Transmitter-Off Current with Watchdog Disabled	Іввто	_	—	100	μΑ	With voltage regulator on, transmitter off, receiver on, FAULT/TxE = VIL, CS = VIH,VREG = 5.0V		
		_	—	100	μΑ	With voltage regulator on, transmitter off, receiver on, FAULT/TxE = VIL, CS = VIH,VREG = 3.3V		
VBB Power-Down Current	IBBPD	_	4.5	8	μA	With voltage regulator powered-off, receiver on and transmitter off, FAULT/TXE = VIH, TXD = VIH, CS = VIL)		
VBB Current with Vss Floating	Ibbnognd	-1	—	1	mA	VBB = 12V, GND to VBB, VLIN = 0-18V		

Note 1: Internal current limited. 2.0 ms maximum recovery time (RLBUS = 0Ω , TX = 0, VLBUS = VBB).

2: Characterized, not 100% tested.

2.3 DC Specifications (Continued)

DC Specifications	Electrical Characteristics: Unless otherwise indicated, all limits are specified for: VBB = 6.0V to 18.0V, TA = -40°C to +125°C CREG = 10 µF							
Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions		
Microcontroller Interface								
High-Level Input Voltage (TxD, FAULT/TxE, WWDTTRIG)	Vih	2.0	_	VREG +0.3	V			
Low-Level Input Voltage (TxD, FAULT/TxE, WWDTTRIG)	VIL	-0.3		0.8	V			
High-Level Input Current (TxD, FAULT/TxE, WWDTTRIG)	Ін	-2.5		0.4	μA	Input voltage = 4.0V. ~800 kΩ internal adaptive pull-up		
Low-Level Input Current (TxD, FAULT/TxE, WWDTTRIG)	lı.	-10		—	μA	Input voltage = 0.5V. ~800 kΩ internal adaptive pull-up		
High-Level Input Voltage (CS/LWAKE)	Vih	2.0	—	VBB	V	Through a current-limiting resistor		
Low-Level Input Voltage (CS/LWAKE)	VIL	-0.3	—	0.8	V			
High-Level Input Current (CS/LWAKE)	Ін	—	Ι	8.0	μA	Input voltage = 0.8 VREG ~1.3 M Ω internal pull- down to Vss		
Low-Level Input Current (CS/LWAKE)	lı.	_	—	5.0	μA	Input voltage = $0.2VREG$ ~1.3 M Ω internal pull- down to Vss		
Low-Level Output Voltage (RxD)	Volrxd	_	_	0.2VREG	V	IOL = 2 mA		
High-Level Output Voltage (RxD)	Vohrxd	0.8VREG	—	_	V	Іон = 2 m A		
Low-Level Output Voltage (FAULT/TxE)	Volod			1.0	V	IOL = 4 mA		
Low-Level Output Voltage (RESET)	Volrst		—	1.0	V	IOL = 4 mA		

Note 1: Internal current limited. 2.0 ms maximum recovery time (RLBUS = 0Ω , Tx = 0, VLBUS = VBB).

2: Characterized, not 100% tested.

2.3	DC Specifications	(Continued)
Z .J	Do opecifications	

DC Specifications	Electrical Characteristics: Unless otherwise indicated, all limits are specified for: VBB = $6.0V$ to $18.0V$, TA = $-40^{\circ}C$ to $+125^{\circ}C$ CREG = $10 \mu\text{F}$							
Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions		
Bus Interface								
High-Level Input Voltage	VIH(LBUS)	0.6 VBB	—	—	V	Recessive state		
Low-Level Input Voltage	VIL(LBUS)	-8	—	0.4 Vbb	V	Dominant state		
Input Hysteresis	VHYS	—	—	0.175 Vвв	V	VIH(LBUS) – VIL(LBUS)		
Low-Level Output Current	IOL(LBUS)	40	-	200	mA	Output voltage = 0.1 VBB, VBB = 12V		
Pull-Up Current on Input	IPU(LBUS)	-180	-	-72	μA	~30 kΩ internal pull-up @ VIH (LBUS) = 0.7 VBB, VBB=12V		
Short-Circuit Current Limit	Isc	50	—	200	mA	(Note 1)		
High-Level Output Voltage	VOH(LBUS)	0.8 VBB	_	VBB	V			
Driver Dominant Voltage	V_LOSUP	—	-	1.1	V	VBB = 7.3V, RLOAD = 1000Ω		
Driver Dominant Voltage	V_HISUP	—	-	1.2	V	Vbb = 18V, RLOAD = 1000Ω		
Input Leakage Current (at the receiver during dominant bus level)	IBUS_PAS_ DOM	-1	-	_	mA	Driver off, VBUS = 0V, VBB = 12V		
Input Leakage Current (at the receiver during recessive bus level)	IBUS_PAS_ REC	-20	-	20	μA	Driver off, 8V < VBB < 18V 8V < VBUS < 18V VBUS ≥ VBB		
Leakage Current (disconnected from ground)	IBUS_NO_G ND	-10	—	+10	μA	GNDDEVICE = VBB, 0V < VBUS < 18V, VBB = 12V		
Leakage Current (disconnected from VBB)	IBUS_NO_P WR	-10	_	+10	μA	VBB = GND, 0 < VBUS < 18V		
Receiver Center Voltage	VBUS_CNT	0.475 Vвв	0.5 Vвв	0.525 VBB	V	VBUS_CNT = (VIL (LBUS) + VIH (LBUS))/2		
Slave Termination	RSLAVE	20	30	47	kΩ	(Note 2)		
Capacitance of slave node	CSLAVE			50	pF	(Note 2)		
Wake-Up Voltage Threshold on LIN Bus	V _{WK(LBUS)}	_	_	3.4	V	Wake up from Power- Down mode (Note 3)		

Note 1: Internal current limited. 2.0 ms maximum recovery time (RLBUS = 0Ω , TX = 0, VLBUS = VBB).

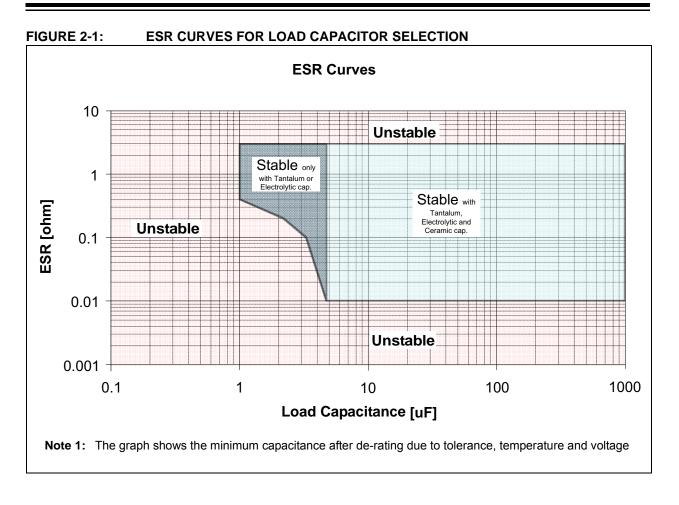
2: Characterized, not 100% tested.

2.3 DC Specifications (Continued)

DC Specifications	Electrical Characteristics: Unless otherwise indicated, all limits are specified for: VBB = 6.0V to 18.0V, TA = -40°C to +125°C CREG = 10 μF						
Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions	
Voltage Regulator – 5.0V							
Output Voltage Range	Vreg	4.85	5.00	5.15	V	0 mA < IOUT < 70 mA	
Line Regulation	ΔVουτ1	—	10	50	mV	IOUT = 1 mA, 6.0V < VBB < 18V	
Load Regulation	ΔΫουτ2	—	10	50	mV	5 mA < IOUT <70 mA 6.0V < VBB < 12V	
Power Supply Ripple Reject	PSRR	—	—	50	dB	1 VPP @10-20 kHz ILOAD = 20 mA	
Output Noise Voltage	eN	_	—	100	µVrмs	10 Hz – 40 MHz Cfilter = 10 μf, Cbp = 0.1 μf, Iload = 20 mA	
Shutdown Voltage Threshold	VSD	3.5	—	4.0	V	See Figure 1-10 (Note 2)	
Input Voltage to Turn Off Output	Voff	3.9	—	4.5	V		
Input Voltage to Turn On Output	Von	5.25	—	6.0	V		
Voltage Regulator – 3.3V							
Output Voltage	Vreg	3.20	3.30	3.40	V	0 mA < IOUT < 70 mA	
Line Regulation	ΔVουτ1	—	10	50	mV	Iout = 1 mA, 6.0V < Vbb < 18V	
Load Regulation	ΔΫΟυτ2	—	10	50	mV	5 mA < IOUT < 70 mA, 6.0V < VBB < 12V	
Power Supply Ripple Reject	PSRR	_	-	50	dB	1 Vpp @10-20 kHz, Iload = 20 mA	
Output Noise Voltage	eN	—	—	100	µVrms /√Hz	10 Hz – 40 MHz Cfilter = 10 μf, Cbp = 0.1 μf, ILOAD = 20 mA	
Shutdown Voltage	VSD	2.5	_	2.7	V	See Figure 1-10 (Note 2)	

Note 1: Internal current limited. 2.0 ms maximum recovery time (RLBUS = 0Ω , TX = 0, VLBUS = VBB).

2: Characterized, not 100% tested.



2.4 AC Specifications

AC CHARACTERISTICS	Electrical Ch VBB = 6.0V to				e indicate	d, all limits are specified for
Parameter	Sym.	Min.	Тур.	Max.	Units	Test Conditions
Bus Interface - Constant Slo	ope Time Para	ameters (D	OC specifi	cations ar	e for a Ve	BB range of 6.0 to 18.0V)
Slope Rising and Falling Edges	t SLOPE	3.5	_	22.5	μs	7.3V <= V _{BB} <= 18V
Propagation Delay of Transmitter	t TRANSPD	_	_	5.0	μs	ttranspd = max (ttranspdr or ttranspdf ₎
Propagation Delay of Receiver	trecpd	_		6.0	μs	tRECPD = max (tRECPDR or tRECPDF)
Symmetry of Propagation Delay of Receiver Rising Edge w.r.t. Falling Edge	trecsym	-2.0		2.0	μs	trecsym = max (tRECPDF – tRECPDR) RRXD 2.4 k Ω to VCC, CRXD 20pF
Symmetry of Propagation Delay of Transmitter Rising Edge w.r.t. Falling Edge	TRANSSYM	-2.0	_	2.0	μs	ttranssym = max (ttranspdf - ttranspdr)
Bus Dominant Time-Out Time	t _{TO(LIN)}		25	_	mS	
Time to Sample of FAULT/TxE for Bus Conflict Reporting	t FAULT	_	_	32.5	μs	tFAULT = max (tTRANSPD + tSLOPE + tRECPD)
Duty Cycle 1 @ 20.0 kbit/sec		0.396	_	_	%tBIT	CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.744 x VBB, THDOM(MAX) = 0.581 x VBB, VBB =7.0V - 18V; tBIT = 50 µS. D1 = tBUS_REC(MIN) / 2 x tBIT)
Duty Cycle 2 @ 20.0 kbit/sec				0.581	%tBIT	CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.284 x VBB, THDOM(MAX) = 0.422 x VBB, VBB =7.6V - 18V; tBIT = 50 µS. D2 = tBUS_REC(MAX) / 2 x tBIT)
Duty Cycle 3 @ 10.4 kbit/sec		0.417	_	_	%tBIT	CBUS;RBUS conditions: 1 nF; 1 k Ω 6.8 nF; 660 Ω 10 nF; 500 Ω THREC(MAX) = 0.778 x VBB, THDOM(MAX) = 0.616 x VBB, VBB =7.0V - 18V; tBIT = 96 µS. D3 = tBUS_REC(MIN) / 2 x tBIT)
Duty Cycle 4 @ 10.4 kbit/sec			_	0.590	%tBIT	$\begin{array}{c} C_{BUS}; RBUS \ conditions: \\ 1 \ nF; \ 1 \ k\Omega \ \ 6.8 \ nF; \\ 660\Omega \ \\ 10 \ nF; \ 500\Omega \\ THREC(MAX) = 0.251 \ x \ VBB, \\ THDOM(MAX) = 0.389 \ x \ VBB, \\ VBB = 7.6V - 18V; \ tBIT = 96 \ \mus. \\ D4 = tBUS_{REC}(MAX) / 2 \ x \ tBIT) \end{array}$

AC CHARACTERISTICS	Electrical Characteristics : Unless otherwise indicated, all limits are specified for $V_{BB} = 6.0V$ to $18.0V$; TA = $-40^{\circ}C$ to $+125^{\circ}C$							
Parameter	Sym.	Min.	Тур.	Max.	Units	Test Conditions		
Voltage Regulator								
Bus Activity Debounce time	t _{BDB}	30	80	250	μs			
Bus Activity to Voltage Regulator Enabled	t _{BACTIVE}	35	—	200	μs			
Voltage Regulator Enabled to Ready	t _{VEVR}	300	_	1200	μs	(Note 1)		
Chip Select to Ready Mode	tCSR	_	_	230	μs			
Chip Select to Power-Down	tCSPD	_	—	300	μs	(Note 2)		
Short-Circuit to Shutdown	t SHUTDOWN	20		100	μs			
RESET Timing								
VREG OK detect to RESET inactive	tRPU	_	_	60.0	μs			
VREG not OK detect to RESET active	tRPD	_	_	60.0	μs			
WWDT								
Reset Pulse Length	twdrst		150	_	μs	-40/+100%		
Power-Up Watchdog Window Length	tPOWERUP	—	27.2	_	ms	±15% RWWDTSELECT = 33 kΩ (Note 2, Note 3)		
Watchdog Window Length	twlength	5.95	7	8.05	ms	±15% RWWDTSELECT = 33 kΩ (Note 4, Note 5)		
		102	120	138	ms	±15% RWWDTSELECT = 680 kΩ (Note 4, Note 5)		

2.4 AC Specifications (Continued)

Note 1: Time depends on external capacitance and load. Test condition: CREG = 4.7uF, no resistor load.

- 2: Characterized, not 100% tested.
- 3: tPOWERUP = 0.8 ms × (RWWDTSELECT+1); R in $k\Omega$.
- 4: twLENGTH = (0.175 ms × RWWDTSELECT) + 1.2 ±15%; R in kΩ.
- 5: Characterized; tested for RWWDTSELECT = 33 k Ω and 680 k Ω

2.5 Thermal Specifications

Parameter	Symbol	Тур	Max	Units	Test Conditions			
Recovery Temperature	θRECOVERY	+140	—	°C				
Shutdown Temperature	0SHUTDOWN	+150	—	°C				
Short Circuit Recovery Time	t THERM	1.5	5.0	ms				
Thermal Package Resistances	Thermal Package Resistances							
Thermal Resistance, 14L-PDIP	θJA	70	—	°C/W				
Thermal Resistance, 14L-SOIC	θJA	90.8	—	°C/W				
Thermal Resistance, 20L-QFN	θJA	44.6	—	°C/W				

Note 1: The maximum power dissipation is a function of TJMAX, ΘJA and ambient temperature T_A. The maximum allowable power dissipation at an ambient temperature is PD = (TJMAX - TA) ΘJA. If this dissipation is exceeded, the die temperature will rise above 150°C and the MCP2050 will go into thermal shutdown.

2.6 Typical Performance Curves

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, VBB = 6.0V to 18.0V; TA = -40°C to +125°C

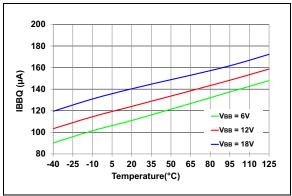


FIGURE 2-2: Typical IBBQ vs. Temperature – 5.0V.

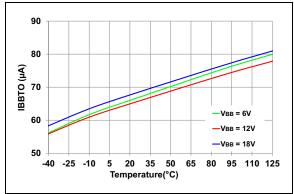


FIGURE 2-3: Typical IBBTO vs. Temperature – 5.0V.

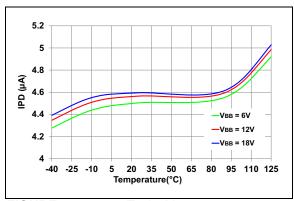


FIGURE 2-4: Typical IPD vs. Temperature – 5.0V.

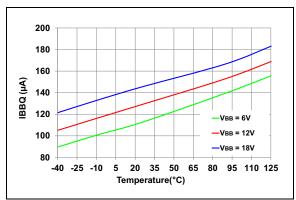


FIGURE 2-5: Typical IBBQ vs. Temperature – 3.3V.

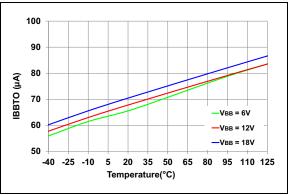


FIGURE 2-6: Typical IBBTO vs. Temperature – 3.3V.

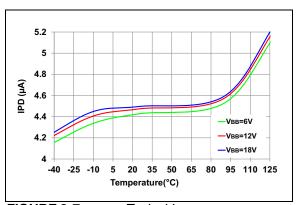
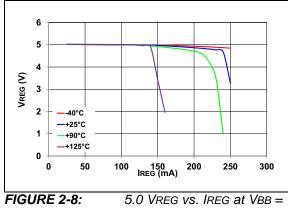
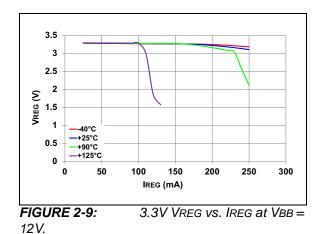


FIGURE 2-7: Typical IPD vs. Temperature – 3.3V.



12V.



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MCP2050

2.7 Timing Diagrams and Specifications

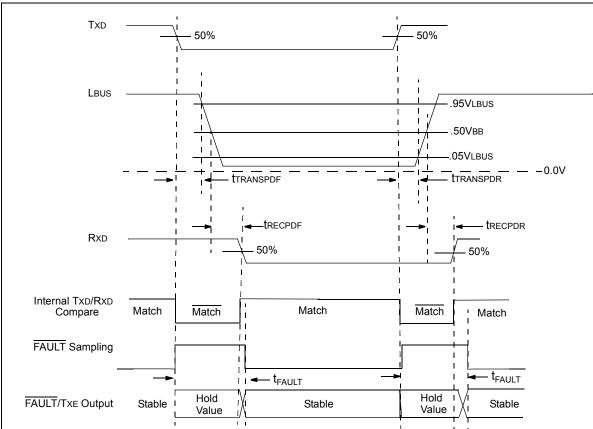
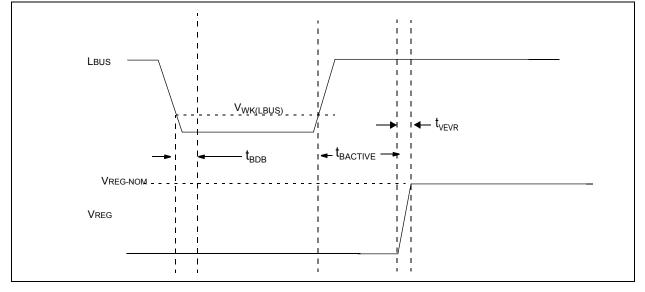
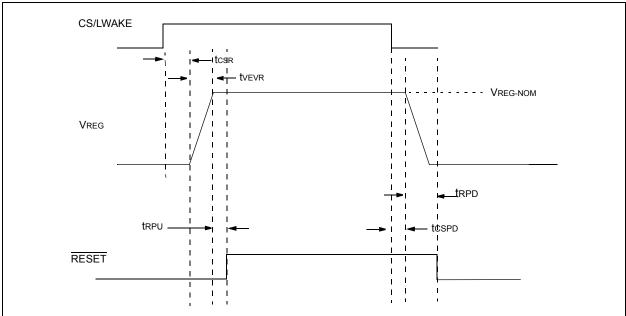


FIGURE 2-10: BUS TIMING DIAGRAM



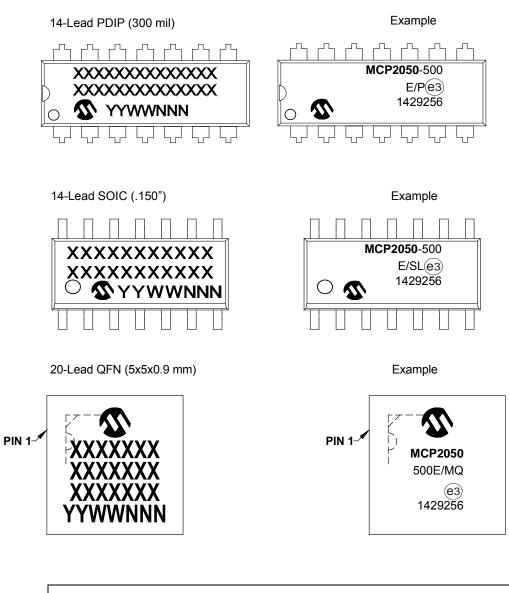




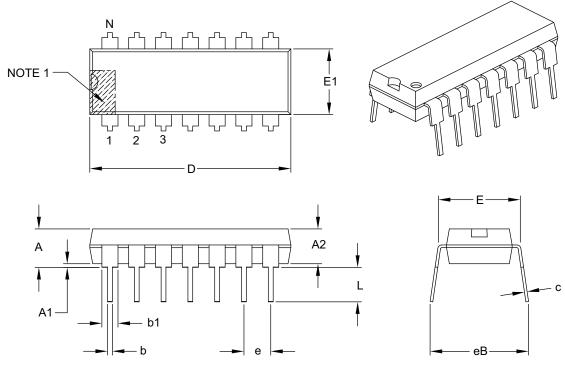


3.0 PACKAGING INFORMATION

3.1 Package Marking Information



Legend	I: XXX Y YY WW NNN @3 *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC [®] designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
Note:	be carrie	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.



For the most current package drawings, please see the Microchip Packaging Specification located at

14-Lead Plastic Dual In-Line (P) – 300 mil Body [PDIP]

http://www.microchip.com/packaging

INCHES Units **Dimension Limits** MIN NOM MAX Number of Pins Ν 14 Pitch .100 BSC е Top to Seating Plane .210 А Molded Package Thickness .115 .130 .195 A2 .015 Base to Seating Plane A1 _ _ .290 Shoulder to Shoulder Width Е .310 .325 .240 .250 .280 Molded Package Width E1 **Overall Length** D .735 .750 .775 Tip to Seating Plane L .115 .130 .150 .008 .010 Lead Thickness .015 С Upper Lead Width b1 .045 .060 .070 Lower Lead Width b .014 .018 .022 Overall Row Spacing § eВ .430

Notes:

Note:

1. Pin 1 visual index feature may vary, but must be located with the hatched area.

2. § Significant Characteristic.

3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.

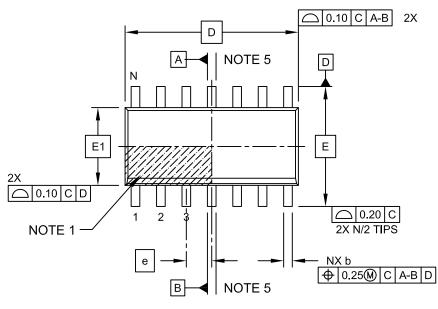
4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

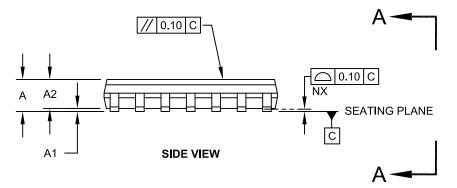
Microchip Technology Drawing C04-005B

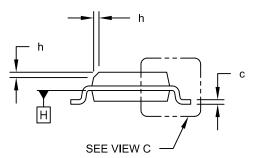
14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging







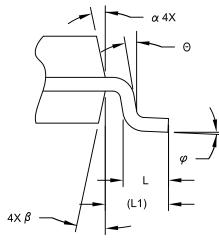


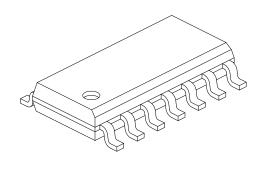
VIEW A-A

Microchip Technology Drawing No. C04-065C Sheet 1 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





V	IEW	С

	MILLIMETERS			
Dimension Lin	nits	MIN	NOM	MAX
Number of Pins	N		14	
Pitch	е		1.27 BSC	
Overall Height	A	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E		6.00 BSC	
Molded Package Width	E1	3.90 BSC		
Overall Length	D	8.65 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40	-	1.27
Footprint	L1		1.04 REF	
Lead Angle	Θ	0°	-	-
Foot Angle	φ	0°	-	8°
Lead Thickness	с	0.10	-	0.25
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

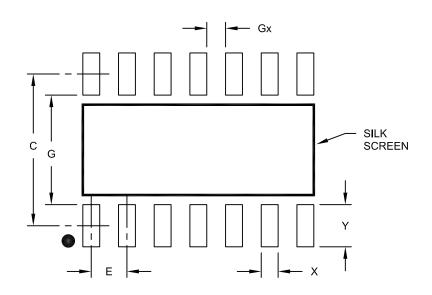
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065C Sheet 2 of 2

14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

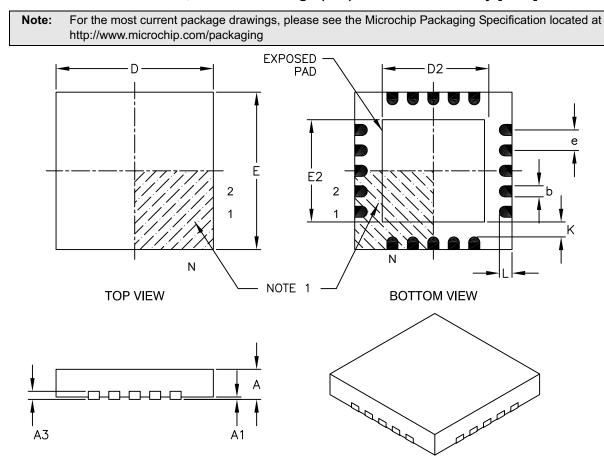
	Units	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX	
Contact Pitch	E		1.27 BSC		
Contact Pad Spacing	С		5.40		
Contact Pad Width	Х			0.60	
Contact Pad Length	Y			1.50	
Distance Between Pads	Gx	0.67			
Distance Between Pads	G	3.90			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065A



20-Lead Plastic Quad Flat, No Lead Package (MQ) – 5x5x0.9 mm Body [QFN]

	Units	MILLIMETERS			
Dimensior	n Limits	MIN	NOM	MAX	
Number of Pins	N		20		
Pitch	е		0.65 BSC		
Overall Height	Α	0.80	0.90	1.00	
Standoff	A1	0.00	0.02	0.05	
Contact Thickness	A3		0.20 REF		
Overall Width	E		5.00 BSC		
Exposed Pad Width	E2	3.15	3.25	3.35	
Overall Length	D		5.00 BSC		
Exposed Pad Length	D2	3.15	3.25	3.35	
Contact Width	b	0.25	0.30	0.35	
Contact Length	L	0.35	0.40	0.45	
Contact-to-Exposed Pad	K	0.20	_	-	

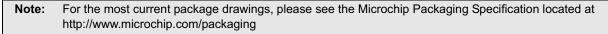
Notes:

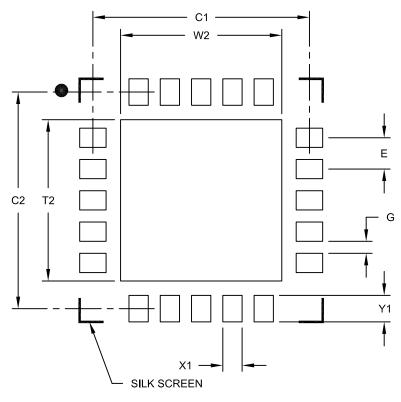
- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package is saw singulated.
- 3. Dimensioning and tolerancing per ASME Y14.5M.
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-139B

20-Lead Plastic Quad Flat, No Lead Package (MQ) - 5x5 mm Body [QFN] With 0.40mm Contact Length





RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimensio	Dimension Limits		NOM	MAX		
Contact Pitch	E		0.65 BSC			
Optional Center Pad Width	W2			3.35		
Optional Center Pad Length	T2			3.35		
Contact Pad Spacing	C1		4.50			
Contact Pad Spacing	C2		4.50			
Contact Pad Width (X20)	X1			0.40		
Contact Pad Length (X20)	Y1			0.55		
Distance Between Pads	G	0.20				

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2139A

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	<u>[X]</u> ⁽¹⁾ =	<u>x /xx</u>	Examples:	
Device	Tape and Reel Tempe Option Ran	-	a) MCP2050-330E/P: 3.3V, Extended Temperature, 14-LD PDI Package	IP
Device:	MCP2050: LIN Transceiver with	Voltago Pogulator	b) MCP2050-330E/MQ: 3.3V, Extended Temperature, 20-LD QFN Package	N
Device.	MCP2050: LIN Transceiver with Voltage Regulator MCP2050T: LIN Transceiver with Voltage Regulator (Tape and Reel) (SOIC and QFN)		c) MCP2050T-330E/MQ: Tape and Reel, 3.3V, Extended Temperature, 20-LD QFN Package	
Tape and Reel Option:	Blank = Standard packaging (tube or tray) T = Tape and Ree ⁽¹⁾		d) MCP2050-330E/SL: 3.3V, Extended Temperature, 14-LD SOI Package	IC
Temperature	$E = -40^{\circ}C \text{ to } +125^{\circ}C$		e) MCP2050T-330E/SL: Tape and Reel, 3.3V, Extended Temperature, 14-LD SOIC Package	
Range:			f) MCP2050-500E/P: 5.0V, Extended Tempera ture, 14-LD PDIP Packag a) MCP2050-500E/MQ: 5.0V, Extended Tempera	ge
Package:	MQ = 20-Lead Plastic Quad Flat	, No Lead Package –	ture, 20-LD QFN Packag	
	5x5x0.9 mm Body (QFN) P = 14-Lead Plastic Dual In-Li	, , ,	h) MCP2050T-500E/MQ: Tape and Reel, 5.0V, Extended Temperature, 20-LD QFN Package	
	SL = 14-Lead Plastic Small Out (SOIC)	line – Narrow, 3.90 mm Body	i) MCP2050-500E/SL: 5.0V, Extended Tempera ture, 14-LD SOIC Packag	
			j) MCP2050T-500E/SL: Tape and Reel, 5.0V, Extended Temperature, 14-LD SOIC package	
			Note 1: Tape and Reel identifier only appears in the catalog part number description. This iden fier is used for ordering purposes and is no printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.	nti- iot h

APPENDIX A: REVISION HISTORY

Revision D (September 2014)

The following is the list of modifications:

- 1. Added Exposed Thermal Pad pin on QFN and in Section 1.3, Pin Descriptions.
- 2. Updated Figure 1-7.
- 3. Added note in Figure 2-1.
- 4. Added AC parameter for WWDT in Section 2.4, AC Specifications.
- 5. Created new Section 2.6, Typical Performance Curves.
- 6. Fixed minor typographical errors.

Revision C (August 2012)

The following is the list of modifications:

1. Removed two notes in Section 2.4 "AC Specifications".

Revision B (April 2012)

The following is the list of modifications:

- 1. Corrected a label in Figure 1-12.
- 2. Corrected a label in Figure 1-13.
- 3. Updated the Product Identification System page.

Revision A (March 2012)

Original release of this document.

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
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